# NRVTSA4100E

# **Trench-Based Schottky Rectifier, Low Leakage**

#### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

#### **Typical Applications**

- Switching Power Supplies including Wireless, Smartphone and Notebook Adapters
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation
- LED Lighting

#### **Mechanical Characteristics:**

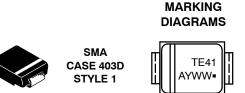
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting SurfaceTemperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



## **ON Semiconductor®**

www.onsemi.com

SCHOTTKY BARRIER RECTIFIERS 4 AMPERES 100 VOLTS



TE41	= Specific Device Code
А	= Assembly Location
Y	= Year

- = Year
- WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping†
NRVTSA4100ET3G	SMA (Pb-Free)	5000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
Average Rectified Forward Current (T <sub>L</sub> = 142°C)	I <sub>F(AV)</sub>	4.0	A
Peak Repetitive Forward Current, (Square Wave, 20 kHz, T <sub>L</sub> = 135°C)	I <sub>FRM</sub>	8.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	150	A
Storage Temperature Range	T <sub>stg</sub>	-65 to +175	°C
Operating Junction Temperature	TJ	-55 to +175	°C
ESD Rating (Human Body Model)		1B	
ESD Rating (Machine Model)		M3	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **THERMAL CHARACTERISTICS**

Characteristic	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Lead, Steady State (Assumes 600 mm <sup>2</sup> 1 oz. copper bond pad, on a FR4 board)	$R_{ extsf{ heta}JL}$	-	16.2	°C/W
Thermal Resistance, Junction-to-Ambient, Steady State (Assumes 600 mm <sup>2</sup> 1 oz. copper bond pad, on a FR4 board)	$R_{ hetaJA}$	-	90	°C/W

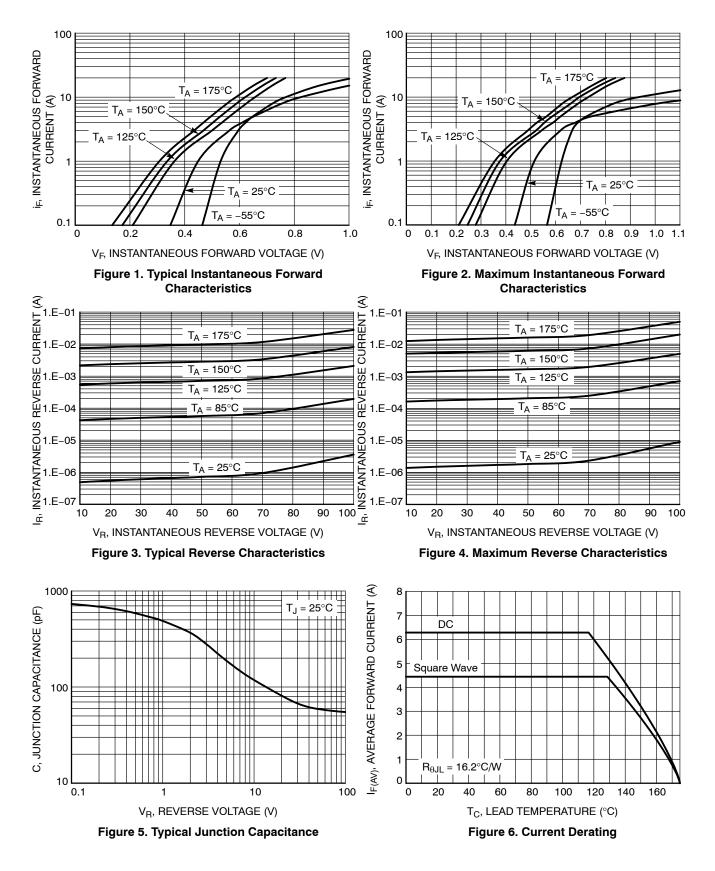
#### **ELECTRICAL CHARACTERISTICS**

Instantaneous Forward Voltage (Note 1)	٧ <sub>F</sub>			V
(i <sub>F</sub> = 1.0 Amps, T <sub>J</sub> = 25°C)		0.45	-	
(i <sub>F</sub> = 4.0 Amps, T <sub>J</sub> = 25°C)		0.61	0.68	
(i <sub>F</sub> = 1.0 Amps, T <sub>J</sub> = 125°C)		0.36	_	
(i <sub>F</sub> = 4.0 Amps, T <sub>J</sub> = 125°C)		0.53	0.59	
Reverse Current (Note 1)	i <sub>R</sub>			
(Rated dc Voltage, T <sub>J</sub> = 25°C)		3.5	29	μΑ
(Rated dc Voltage, $T_J = 125^{\circ}C$ )		2.0	5.0	mA
Diode Capacitance	C <sub>d</sub>			pF
(Rated dc Voltage, T <sub>J</sub> = 25°C, f = 1 MHz)		55		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2.0%.

## NRVTSA4100E

### **TYPICAL CHARACTERISTICS**



## NRVTSA4100E

### **TYPICAL CHARACTERISTICS**

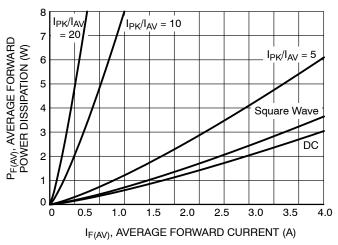


Figure 7. Forward Power Dissipation

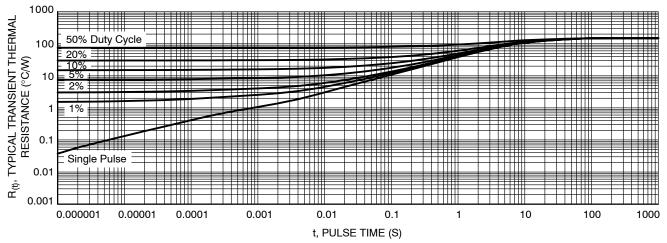


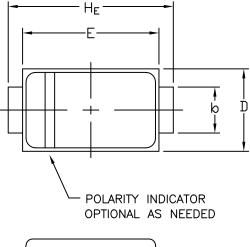
Figure 8. Typical Transient Thermal Response, Junction-to-Ambient

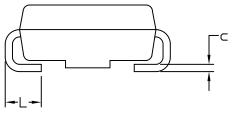
#### **MECHANICAL CASE OUTLINE** PACKAGE DIMENSIONS

# onsemi



STYLE 1 STYLE 2 SCALE 1:1

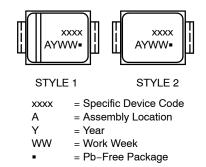




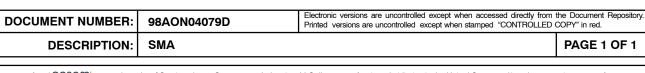


A1

#### GENERIC **MARKING DIAGRAM\***



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



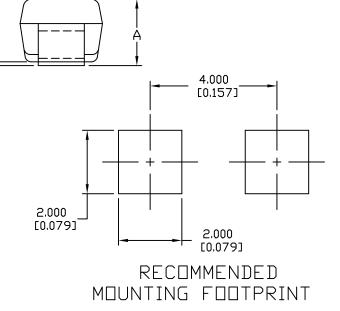
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

DATE 22 OCT 2021

#### NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCHES
- DIMENSION & SHALL BE MEASURED WITHIN DIMENSION L. З.

	MILLIMETERS			INCHES		
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
A	1.97	2.10	2.20	0.078	0.083	0.087
A1	0.05	0.10	0.20	0.002	0.004	0.008
Ø	1.27	1.45	1.63	0.050	0.057	0.064
С	0.15	0.28	0.41	0.006	0.011	0.016
D	2.29	2.60	2.92	0.090	0.103	0.115
E	4.06	4.32	4.57	0.160	0.170	0.180
HE	4.83	5.21	5.59	0.190	0.205	0.220
L	0.76	1.14	1.52	0.030	0.045	0.060



onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

#### TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Schottky Diodes & Rectifiers category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

MA4E2039 D1FH3-5063 MBR0530L-TP MBR10100CT-BP MBR1545CT MMBD301M3T5G RB160M-50TR RB551V-30 BAS16E6433HTMA1 BAT 54-02LRH E6327 NSR05F40QNXT5G NTE555 JANS1N6640 SB07-03C-TB-H SB1003M3-TL-W SK310-T SK32A-LTP SK34B-TP SS3003CH-TL-E GA01SHT18 CRS10I30A(TE85L,QM MA4E2501L-1290 MBRB30H30CT-1G SB007-03C-TB-E SK32A-TP SK33B-TP SK38B-TP NRVBM120LT1G NTE505 NTSB30U100CT-1G SS15E-TP VS-6CWQ10FNHM3 ACDBA1100LR-HF ACDBA1200-HF ACDBA140-HF ACDBA2100-HF ACDBA3100-HF CDBQC0530L-HF ACDBA340-HF ACDBA260LR-HF ACDBA1100-HF SK310B-TP MA4E2502L-1246 MA4E2502H-1246 NRVBM120ET1G NSR01L30MXT5G NTE573 NTE6081 SB560 PMAD1108-LF